

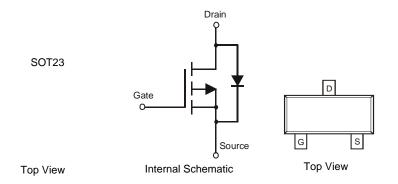
P-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Low R_{DS(ON)}:
 - 75 mΩ $@V_{GS} = -4.5V$
 - 110 m Ω @V_{GS} = -2.7V
 - 125 m Ω @V_{GS} = -2.5V
- Low Input/Output Leakage
- Lead, Halogen and Antimony Free, RoHS Compliant "Green" Device (Notes 1, 2 and 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT23
- Case Material Molded Plastic, "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram Below
- Weight: 0.008 grams (approximate)



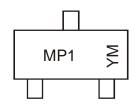
Ordering Information (Note 4)

Part Number	Case	Packaging
DMP2130L-7	SOT23	3000/Tape & Reel

Notes:

- No purposefully added lead. Halogen and Antimony Free.
 Diodes Inc's "Green" policy can be found on our website at http://www.diodes.com.
- 3. Product manufactured with Green Molding Compound and does not contain Halogens or Sb₂O₃ Fire Retardants.
- 4. For packaging details, go to our website at http://www.diodes.com.

Marking Information



MP1 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: U = 2007)M = Month (ex: 9 = September)

Date Code Key

Year	20	07	20	08	20	09	20	10	20	11	20	12
Code	Ų	J	\	/	V	V)	(`	1	Ž	7_
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings @T_A = 25℃ unless otherwise specified

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage		V_{DSS}	-20	V
Gate-Source Voltage		V_{GSS}	±12	V
Drain Current (Note 5) Continuous	T _A = 25℃ T _A = 70℃	ID	-3.0 -2.4	А
Pulsed Drain Current (Note 6)		I _{DM}	-15	Α
Body-Diode Continuous Current (Note 5)		Is	2.0	Α

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P_{D}	1.4	W
Thermal Resistance, Junction to Ambient (Note 5); Steady-State	$R_{ hetaJA}$	90	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

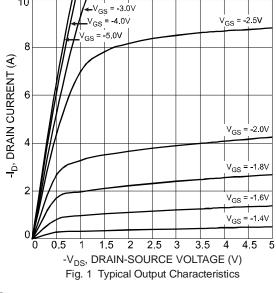
Electrical Characteristics @TA = 25°C unless otherwise specified

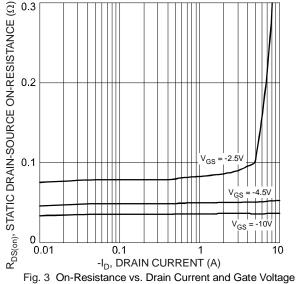
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
STATIC PARAMETERS				1			
Drain-Source Breakdown Voltage	BV _{DSS}	-20	_	_	V	$I_D = -250 \mu A, V_{GS} = 0V$	
Zero Gate Voltage Drain Current T _J = 25°C	I _{DSS}	_	_	-1	μΑ	$V_{DS} = -20V, V_{GS} = 0V$	
Gate-Body Leakage Current	I _{GSS}	_	_	±100	nA	$V_{DS} = 0V, V_{GS} = \pm 12V$	
Gate Threshold Voltage	V _{GS(th)}	-0.6	_	-1.25	V	$V_{DS} = V_{GS}$, $I_D = -250\mu A$	
On State Drain Current (Note 7)	I _{D (ON)}	-15	_		Α	$V_{GS} = -4.5V, V_{DS} = -5V$	
			51	75		$V_{GS} = -4.5V$, $I_D = -3.5A$	
Static Drain-Source On-Resistance (Note 7)	R _{DS (ON)}	_	87	110	mΩ	$V_{GS} = -2.7V, I_D = -3.0A$	
			99	125		$V_{GS} = -2.5V, I_D = -2.6A$	
Forward Transconductance (Note 7)	g FS	_	7.3	_	S	$V_{DS} = -10V, I_{D} = -3.0A$	
Diode Forward Voltage (Note 7)	V_{SD}	_	0.79	-1.26	V	$I_S = -1.7A$, $V_{GS} = 0V$	
Maximum Body-Diode Continuous Current (Note 5)	Is	_	_	1.7	Α	_	
DYNAMIC PARAMETERS (Note 8)							
Total Gate Charge	Q_g	_	7.3	_	nC	$V_{GS} = -4.5V$, $V_{DS} = -10V$, $I_{D} = -3.0A$	
Gate-Source Charge	Q_{gs}	_	2.0	_	nC	$V_{GS} = -4.5V$, $V_{DS} = -10V$, $I_{D} = -3.0A$	
Gate-Drain Charge	Q_{gd}	_	1.9		nC	$V_{GS} = -4.5V$, $V_{DS} = -10V$, $I_{D} = -3.0A$	
Turn-On Delay Time	t _{D(on)}	_	12	_	ns		
Turn-On Rise Time		_	20	_	ns	$V_{DS} = -10V, V_{GS} = -4.5V,$	
Turn-Off Delay Time		_	38	_	ns	$R_L = 10\Omega$, $R_G = 6\Omega$	
Turn-Off Fall Time	t _f	_	41	_	ns		
Input Capacitance		_	443	_	pF	V 46V V 6V	
Output Capacitance			128		pF	$V_{DS} = -16V, V_{GS} = 0V$ f = 1.0MHz	
Reverse Transfer Capacitance	C_{rss}	_	101	—	pF	1 - 1.01/11 12	

Notes:

- 5. Device mounted on 1"x1", FR-4 PC board with 2 oz. Copper and test pulse width t \leq 10s. 6. Repetitive Rating, pulse width limited by junction temperature. 7. Test pulse width t = 300 μs . 8. Guaranteed by design. Not subject to production testing.







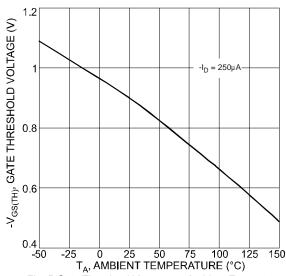
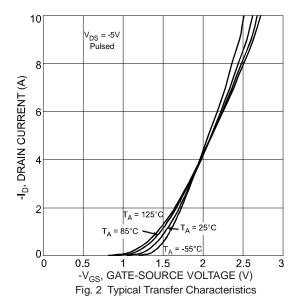
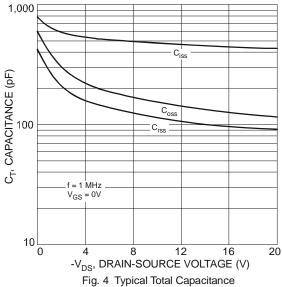


Fig. 5 Gate Threshold Voltage vs. Ambient Temperature





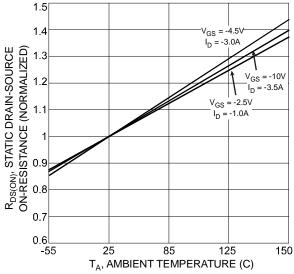
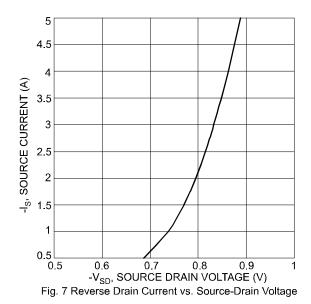
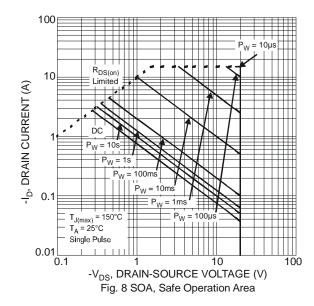


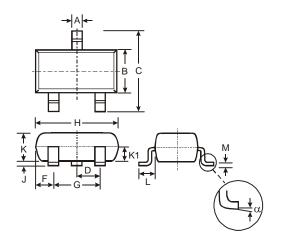
Fig. 6 Normalized Static Drain-Source On-Resistance vs. Ambient Temperature





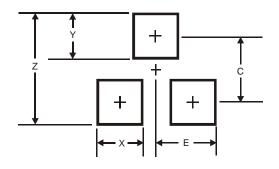


Package Outline Dimensions



SOT23						
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
C	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Н	2.80	3.00	2.90			
7	0.013	0.10	0.05			
K	0.903	1.10	1.00			
K1	-	-	0.400			
L	0.45	0.61	0.55			
М	0.085	0.18	0.11			
α	0°	8°	-			
All	All Dimensions in mm					

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
X	0.8
Υ	0.9
С	2.0
E	1.35



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